

Page 40, lines 18-22:

B14 (5) A porous metal plate made from powdered tungsten of mean particle size of $3.0\ \mu\text{m}$ sintered at 1900°C was mounted on the ceramic substrate as described in (4) above, by means of silver soldering paste, and bonded by heating to a temperature of 970°C (see Fig. 11C).

IN THE DRAWINGS:

Please correct Figures 1A-3, 5A-B and 6A-9, 11 and 13 as set forth in the attached Request for Approval of Drawing Corrections.

IN THE TITLE:

Please replace the Title so that it reads as follows:

CERAMIC HEATER WITH OFFSET ELECTRIC HEATING ELEMENTS IN THE THICKNESS DIRECTION.

IN THE CLAIMS:

Please replace claims 11-28 as follows:

- B17
11. (Amended) A ceramic heater for a wafer, comprising:
a disk-shaped ceramic substrate; and
a heat generation pattern disposed within said disk-shaped ceramic substrate,
at least part of said heat generation pattern being disposed on an offset level different from that of others of said heat generation pattern in the direction of thickness of said ceramic substrate.
12. (Amended) The ceramic heater for a wafer according to claim 11, wherein said heat generation pattern are disposed such that a level of adjoining ones to others is offset in the direction of thickness of said ceramic substrate.
13. (Amended) The ceramic heater for a wafer according to claim 11 or 12, wherein said heat generation means is flat in cross-section.

14. (Amended) The ceramic heater for a wafer according to claim 13, wherein an amount of offset displacement in level of a mutually adjacent heat generation pattern is in a range of 1 to 100 μm .

15. (Amended) The ceramic heater for a wafer according to claim 14, wherein a maximum amount of offset displacement of said heat generation pattern is in the range of 3 to 500 μm .

16. (Amended) The ceramic heater for a wafer according to claim 13, wherein a maximum amount of offset displacement of said heat generation pattern is in the range of 3 to 500 μm .

17. (Amended) The ceramic heater for a wafer according to claim 11 or 12, wherein an amount of offset displacement in level of a mutually adjacent heat generation pattern is in a range of 1 to 100 μm .

18. (Amended) The ceramic heater for a wafer according to claim 17, wherein a maximum amount of offset displacement of said heat generation pattern is in a range of 3 to 500 μm .

19. (Amended) The ceramic heater for a wafer according to claim 11 or 12, wherein a maximum amount of offset displacement of said heat generation pattern is in a range of 3 to 500 μm .

20. (Amended) The ceramic heater for a wafer according to claim 11 or 12, wherein said heat generation pattern comprises a spiral wire body.

21. (Amended) The ceramic heater for a wafer according to claim 20, wherein an amount of offset displacement in level of a mutually adjacent heat generation pattern is in a range of 1 to 500 μm .

22. (Amended) The ceramic heater for a wafer according to claim 21, wherein a maximum amount of offset displacement of said heat generation pattern is in a range of 5 to 2000 μm .

23. (Amended) The ceramic heater for a wafer according to claim 20, wherein a maximum amount of offset displacement of said heat generation pattern is in a range of 5 to 2000 μm .

24. (Amended) The ceramic heater for a wafer according to claim 11 or 12, wherein an amount of offset displacement in level of a mutually adjacent heat generation pattern is in a range of 1 to 500 μm .

25. (Amended) The ceramic heater for a wafer according to claim 24, wherein a maximum amount of offset displacement of said heat generation pattern is in a range of 5 to 2000 μm .

26. (Amended) The ceramic heater for a wafer according to claim 11 or 12, wherein a maximum amount of offset displacement of said heat generation pattern is in a range of 5 to 2000 μm .

27. (Amended) The ceramic heater for a wafer according to claim 11 or 12, wherein electrostatic electrodes are provided on said ceramic substrate.

28. (Amended) The ceramic heater for a wafer according to claim 11 or 12, wherein a chuck-top conductor layer is formed on a surface of said ceramic substrate.

REMARKS

Claims 11-28 are pending. By this Amendment, claims 11-28 are amended. Claim 11 is amended to recite "heat generation pattern" to use different language but not for substantial reasons of patentability. This amendment explicitly recites what was implicit in the "heat generation means." Claims 12-28 are amended to be consistent with amended claim 11.